

Holger von Wenckstern

List of Publications by Citations

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159
papers

4,662
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163
ext. papers

5,087
ext. citations

3.5
avg, IF

5.66
L-index

#	Paper	IF	Citations
159	High electron mobility of epitaxial ZnO thin films on c-plane sapphire grown by multistep pulsed-laser deposition. <i>Applied Physics Letters</i> , 2003 , 82, 3901-3903	3.4	539
158	Mean barrier height of Pd Schottky contacts on ZnO thin films. <i>Applied Physics Letters</i> , 2006 , 88, 092102	3.4	146
157	Optical and electrical properties of epitaxial (Mg,Cd) _x Zn _{1-x} O, ZnO, and ZnO:(Ga,Al) thin films on c-plane sapphire grown by pulsed laser deposition. <i>Solid-State Electronics</i> , 2003 , 47, 2205-2209	1.7	130
156	Defects in virgin and N ⁺ -implanted ZnO single crystals studied by positron annihilation, Hall effect, and deep-level transient spectroscopy. <i>Physical Review B</i> , 2006 , 74,	3.3	129
155	Group-III Sesquioxides: Growth, Physical Properties and Devices. <i>Advanced Electronic Materials</i> , 2017 , 3, 1600350	6.4	127
154	Recent progress on ZnO-based metal-semiconductor field-effect transistors and their application in transparent integrated circuits. <i>Advanced Materials</i> , 2010 , 22, 5332-49	24	122
153	Transparent semiconducting oxides: materials and devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1437-1449	1.6	120
152	Transparent p-CuI/n-ZnO heterojunction diodes. <i>Applied Physics Letters</i> , 2013 , 102, 092109	3.4	114
151	Cuprous iodide as p-type transparent semiconductor: history and novel applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 1671-1703	1.6	111
150	Phosphorus acceptor doped ZnO nanowires prepared by pulsed-laser deposition. <i>Nanotechnology</i> , 2007 , 18, 455707	3.4	96
149	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial β -Ga ₂ O ₃ thin films grown by pulsed laser deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 40-47	1.6	95
148	Lateral homogeneity of Schottky contacts on n-type ZnO. <i>Applied Physics Letters</i> , 2004 , 84, 79-81	3.4	95
147	Epitaxial stabilization of pseudomorphic β -Ga ₂ O ₃ on sapphire (0001). <i>Applied Physics Express</i> , 2015 , 8, 011101	2.4	82
146	Optical signatures of deep level defects in Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2018 , 112, 242102	3.4	82
145	Anionic and cationic substitution in ZnO. <i>Progress in Solid State Chemistry</i> , 2009 , 37, 153-172	8	81
144	Control of the conductivity of Si-doped β -Ga ₂ O ₃ thin films via growth temperature and pressure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 34-39	1.6	79
143	Properties of reactively sputtered Ag, Au, Pd, and Pt Schottky contacts on n-type ZnO. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1769		68

142	Electrical and magnetic properties of RE-doped ZnO thin films (RE = Gd, Nd). <i>Superlattices and Microstructures</i> , 2007 , 42, 231-235	2.8	67
141	Oxide bipolar electronics: materials, devices and circuits. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 213001	3	67
140	Deep acceptor states in ZnO single crystals. <i>Applied Physics Letters</i> , 2006 , 89, 092122	3.4	63
139	Tin-assisted heteroepitaxial PLD-growth of Ga_2O_3 thin films with high crystalline quality. <i>APL Materials</i> , 2019 , 7, 022516	5.7	63
138	ZnO metal-semiconductor field-effect transistors with Ag-Schottky gates. <i>Applied Physics Letters</i> , 2008 , 92, 192108	3.4	62
137	Lattice parameters and Raman-active phonon modes of $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$. <i>Journal of Applied Physics</i> , 2015 , 117, 125703	2.5	59
136	Correlation of pre-breakdown sites and bulk defects in multicrystalline silicon solar cells. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 70-72	2.5	57
135	Defects in hydrothermally grown bulk ZnO. <i>Applied Physics Letters</i> , 2007 , 91, 022913	3.4	49
134	Donor-like defects in ZnO substrate materials and ZnO thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 135-139	2.6	47
133	Interface recombination current in type II heterostructure bipolar diodes. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 14785-9	9.5	45
132	Lattice parameters and Raman-active phonon modes of $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ for x. <i>Journal of Applied Physics</i> , 2014 , 116, 013505	2.5	45
131	p-type conducting ZnO:P microwires prepared by direct carbothermal growth. <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 37-39	2.5	44
130	All Amorphous Oxide Bipolar Heterojunction Diodes from Abundant Metals. <i>Advanced Electronic Materials</i> , 2015 , 1, 1400023	6.4	41
129	Strain distribution in bent ZnO microwires. <i>Applied Physics Letters</i> , 2011 , 98, 031105	3.4	41
128	Highly rectifying p-ZnCo ₂ O ₄ /n-ZnO heterojunction diodes. <i>Applied Physics Letters</i> , 2014 , 104, 022104	3.4	40
127	Comparison of Schottky contacts on Gallium oxide thin films and bulk crystals. <i>Applied Physics Express</i> , 2015 , 8, 121102	2.4	40
126	Homoepitaxy of ZnO by pulsed-laser deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , 2007 , 1, 129-131	2.5	38
125	Room-temperature ferromagnetic Mn-alloyed ZnO films obtained by pulsed laser deposition. <i>Journal of Magnetism and Magnetic Materials</i> , 2006 , 307, 212-221	2.8	38

124	Identification of pre-breakdown mechanism of silicon solar cells at low reverse voltages. <i>Applied Physics Letters</i> , 2010 , 97, 073506	3.4	37
123	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2160-2164	2.9	33
122	Morphological, structural and electrical investigations on non-polar a-plane ZnO epilayers. <i>Journal of Crystal Growth</i> , 2010 , 312, 2078-2082	1.6	33
121	A comparison between ZnO films doped with 3d and 4f magnetic ions. <i>Thin Solid Films</i> , 2007 , 515, 8761-8763	3.3	33
120	Visible-blind and solar-blind ultraviolet photodiodes based on (In _x Ga _{1-x}) ₂ O ₃ . <i>Applied Physics Letters</i> , 2016 , 108, 123503	3.4	33
119	Monolithic Multichannel Ultraviolet Photodiodes Based on (Mg,Zn)O Thin Films With Continuous Composition Spreads. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014 , 20, 106-111	3.8	31
118	Rectifying semiconductor-ferroelectric polarization loops and offsets in Pt/BaTiO ₃ /ZnO/Pt thin film capacitor structures. <i>Thin Solid Films</i> , 2005 , 486, 153-157	2.2	31
117	Formation of a two-dimensional electron gas in ZnO/MgZnO single heterostructures and quantum wells. <i>Thin Solid Films</i> , 2009 , 518, 1048-1052	2.2	30
116	Optical properties of homo- and heteroepitaxial ZnO/Mg _x Zn _{1-x} O single quantum wells grown by pulsed-laser deposition. <i>Journal of Luminescence</i> , 2010 , 130, 520-526	3.8	30
115	Method of choice for fabrication of high-quality ZnO-based Schottky diodes. <i>Journal of Applied Physics</i> , 2014 , 116, 194506	2.5	29
114	Tungsten oxide as a gate dielectric for highly transparent and temperature-stable zinc-oxide-based thin-film transistors. <i>Advanced Materials</i> , 2011 , 23, 5383-6	2.4	29
113	Wavelength selective metal-semiconductor-metal photodetectors based on (Mg,Zn)O-heterostructures. <i>Applied Physics Letters</i> , 2011 , 99, 083502	3.4	29
112	Energy-selective multichannel ultraviolet photodiodes based on (Mg,Zn)O. <i>Applied Physics Letters</i> , 2013 , 103, 171111	3.4	27
111	High electron mobility of phosphorous-doped homoepitaxial ZnO thin films grown by pulsed-laser deposition. <i>Journal of Applied Physics</i> , 2008 , 104, 013708	2.5	27
110	Photocurrent spectroscopy of deep levels in ZnO thin films. <i>Physical Review B</i> , 2007 , 76,	3.3	27
109	Electronic properties of defects in pulsed-laser deposition grown ZnO with levels at 300 and 370meV below the conduction band. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 378-381	2.8	27
108	ZnO-Based n-Channel Junction Field-Effect Transistor With Room-Temperature-Fabricated Amorphous p-Type $\text{hbox{ZnCo}}_{2}\text{hbox{O}}_{4}$ Gate. <i>IEEE Electron Device Letters</i> , 2012 , 33, 676-678	4.4	26
107	Electrical properties of ZnO thin films and optical properties of ZnO-based nanostructures. <i>Superlattices and Microstructures</i> , 2005 , 38, 317-328	2.8	25

106	Properties of phosphorus doped ZnO. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 125-128	24
105	Structural, optical, and electrical properties of orthorhombic $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ thin films. <i>APL Materials</i> , 2019 , 7, 022525	5.7 24
104	Epitaxial stabilization of single phase $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ thin films up to $x = 0.28$ on c-sapphire and $\text{Ga}_2\text{O}_3(001)$ templates by tin-assisted VCCS-PLD. <i>APL Materials</i> , 2019 , 7, 101102	5.7 24
103	pn-Heterojunction Diodes with n-Type In_2O_3 . <i>Advanced Electronic Materials</i> , 2015 , 1, 1400026	6.4 23
102	Influence of Oxygen Deficiency on the Rectifying Behavior of Transparent-Semiconducting-Oxide/Metal Interfaces. <i>Physical Review Applied</i> , 2018 , 9,	4.3 23
101	Comparison of ZnO-Based JFET, MESFET, and MISFET. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1828-1833	2.9 21
100	High-gain integrated inverters based on ZnO metal-semiconductor field-effect transistor technology. <i>Applied Physics Letters</i> , 2010 , 96, 113502	3.4 21
99	Characterization of the postjunctional α 2C-adrenoceptor mediating vasoconstriction to UK14304 in porcine pulmonary veins. <i>British Journal of Pharmacology</i> , 2007 , 151, 186-94	8.6 21
98	Room-temperature cathodoluminescence of n-type ZnO thin films grown by pulsed laser deposition in N_2 , N_2O , and O_2 background gas. <i>Thin Solid Films</i> , 2005 , 486, 205-209	2.2 20
97	Defect properties of ZnO and ZnO:P microwires. <i>Journal of Applied Physics</i> , 2011 , 109, 013712	2.5 19
96	Electrical Properties of Vertical p-NiO/n-Ga $_2$ O $_3$ and p-ZnCo $_2$ O $_4$ /n-Ga $_2$ O $_3$ pn-Heterodiodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800729	1.6 18
95	Transparent JFETs Based on p-NiO/n-ZnO Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3999-4003	2.9 18
94	Carrier redistribution in organic/inorganic (poly(3,4-ethylenedioxy thiophene/poly(styrenesulfonate)polymer)-Si) heterojunction determined from infrared ellipsometry. <i>Applied Physics Letters</i> , 2004 , 84, 1311-1313	3.4 18
93	Combinatorial Material Science and Strain Engineering Enabled by Pulsed Laser Deposition Using Radially Segmented Targets. <i>ACS Combinatorial Science</i> , 2018 , 20, 643-652	3.9 18
92	Method of choice for the fabrication of high-quality gallium oxide-based Schottky diodes. <i>Semiconductor Science and Technology</i> , 2017 , 32, 065013	1.8 17
91	Solubility limit and material properties of a $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ thin film with a lateral cation gradient on (00.1) Al_2O_3 by tin-assisted PLD. <i>APL Materials</i> , 2020 , 8, 021103	5.7 17
90	Stable p-type ZnO:P nanowire/n-type ZnO:Ga film junctions, reproducibly grown by two-step pulsed laser deposition. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1693	17
89	Defects in a nitrogen-implanted ZnO thin film. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1220-1236	17

88	Comparative characterization of differently grown ZnO single crystals by positron annihilation and Hall effect. <i>Superlattices and Microstructures</i> , 2007 , 42, 259-264	2.8	17
87	Epitaxial $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ thin films and heterostructures grown by tin-assisted VCCS-PLD. <i>APL Materials</i> , 2019 , 7, 111110	5.7	17
86	Schottky barrier diodes based on room temperature fabricated amorphous zinc tin oxide thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700210	1.6	16
85	Suppression of Grain Boundary Scattering in Multifunctional p-Type Transparent CuI Thin Films due to Interface Tunneling Currents. <i>Advanced Materials Interfaces</i> , 2018 , 5, 1701411	4.6	16
84	Dependence of Trap Concentrations in ZnO Thin Films on Annealing Conditions. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 2861-2863	0.6	16
83	Ultrathin gate-contacts for metal-semiconductor field-effect transistor devices: An alternative approach in transparent electronics. <i>Journal of Applied Physics</i> , 2010 , 107, 114515	2.5	15
82	Identification of a Deep Acceptor Level in ZnO Due to Silver Doping. <i>Journal of Electronic Materials</i> , 2010 , 39, 577-583	1.9	15
81	A Review of the Segmented-Target Approach to Combinatorial Material Synthesis by Pulsed-Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900626	1.3	14
80	Influence of the Cation Ratio on Optical and Electrical Properties of Amorphous Zinc-Tin-Oxide Thin Films Grown by Pulsed Laser Deposition. <i>ACS Combinatorial Science</i> , 2016 , 18, 188-94	3.9	14
79	Long-throw magnetron sputtering of amorphous ZnSnO thin films at room temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1482-1486	1.6	14
78	All-Oxide Inverters Based on ZnO Channel JFETs With Amorphous ZnCo_2O_4 Gates. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 4004-4008	2.9	14
77	ZnO-based metal-semiconductor field-effect transistors on glass substrates. <i>Applied Physics Letters</i> , 2009 , 95, 153503	3.4	14
76	Deep defects generated in n-conducting ZnO:TM thin films. <i>Solid State Communications</i> , 2006 , 137, 417-421	1.2	14
75	Electro-optical properties of ZnO-BaTiO ₃ -ZnO heterostructures grown by pulsed laser deposition. <i>Annalen Der Physik</i> , 2004 , 13, 61-62	2.6	14
74	$\text{SnO}/\text{Ga}_2\text{O}_3$ vertical pn heterojunction diodes. <i>Applied Physics Letters</i> , 2020 , 117, 252106	3.4	14
73	High mobility, highly transparent, smooth, p-type CuI thin films grown by pulsed laser deposition. <i>APL Materials</i> , 2020 , 8, 091115	5.7	14
72	Influence of Oxygen Pressure on Growth of Si-Doped $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ Thin Films on c-Sapphire Substrates by Pulsed Laser Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3217-Q3220 ³	2.3	13
71	Doping efficiency and limits in $(\text{Mg,Zn})\text{O}:\text{Al,Ga}$ thin films with two-dimensional lateral composition spread. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 2850-2855	1.6	13

70	Control of phase formation of $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ thin films on c-plane Al_2O_3 . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 485105	3	13
69	Defect Manipulation To Control ZnO Micro-/Nanowire-Metal Contacts. <i>Nano Letters</i> , 2018 , 18, 6974-6980	1.5	13
68	Defects in zinc-implanted ZnO thin films. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1597		12
67	Dielectric Passivation of ZnO-Based Schottky Diodes. <i>Journal of Electronic Materials</i> , 2010 , 39, 559-562	1.9	12
66	Eclipse Pulsed Laser Deposition for Damage-Free Preparation of Transparent ZnO Electrodes on Top of Organic Solar Cells. <i>Advanced Functional Materials</i> , 2015 , 25, 4321-4327	15.6	11
65	Growth, structural and optical properties of coherent $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3/\text{Ga}_2\text{O}_3$ quantum well superlattice heterostructures. <i>APL Materials</i> , 2020 , 8, 051112	5.7	11
64	On the T2 trap in zinc oxide thin films. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 588-595	1.3	10
63	Semitransparent ZnO-based UV-active solar cells: Analysis of electrical loss mechanisms. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 04J107	1.3	10
62	Single Metal Ohmic and Rectifying Contacts to ZnO Nanowires: A Defect Based Approach. <i>Annalen Der Physik</i> , 2018 , 530, 1700335	2.6	10
61	Low-Voltage Operation of Ring Oscillators Based on Room-Temperature-Deposited Amorphous Zinc-Tin-Oxide Channel MESFETs. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900548	6.4	9
60	Valence band offsets for ALD SiO_2 and Al_2O_3 on $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.25$ - 0.74 . <i>APL Materials</i> , 2019 , 7, 071115	5.7	9
59	Full-Swing, High-Gain Inverters Based on ZnSnO JFETs and MESFETs. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 3376-3381	2.9	9
58	MgZnO/ZnO quantum well nanowire heterostructures with large confinement energies. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011 , 29, 03A104	2.9	9
57	Structural and Elastic Properties of $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ Thin Films on (11.0) Al_2O_3 Substrates for the Entire Composition Range. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000394	1.3	9
56	MESFETs and inverters based on amorphous zinc-tin-oxide thin films prepared at room temperature. <i>Applied Physics Letters</i> , 2018 , 113, 133501	3.4	9
55	Low voltage, high gain inverters based on amorphous zinc tin oxide on flexible substrates. <i>APL Materials</i> , 2020 , 8, 061112	5.7	8
54	Band Alignment of Atomic Layer Deposited SiO_2 and Al_2O_3 on $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.2$ - 0.65 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P351-P356	2	8
53	Low rate deep level transient spectroscopy - a powerful tool for defect characterization in wide bandgap semiconductors. <i>Solid-State Electronics</i> , 2014 , 92, 40-46	1.7	8

52	Transparent Rectifying Contacts for Visible-Blind Ultraviolet Photodiodes Based on ZnO. <i>Journal of Electronic Materials</i> , 2011 , 40, 473-476	1.9	8
51	Semiconducting oxide heterostructures. <i>Semiconductor Science and Technology</i> , 2011 , 26, 014040	1.8	8
50	Homoepitaxial Mg _x Zn _{1-x} O (0 ≤ x ≤ 0.22) thin films grown by pulsed laser deposition. <i>Thin Solid Films</i> , 2010 , 518, 4623-4629	2.2	8
49	Vital Role of Oxygen for the Formation of Highly Rectifying Schottky Barrier Diodes on Amorphous Zinc-Tin-Oxide with Various Cation Compositions. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 26574-26587	2.5	7
48	Dopant activation in homoepitaxial MgZnO:P thin films. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1604		7
47	Progression of group-III sesquioxides: epitaxy, solubility and desorption. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 223001	3	7
46	Effects of alloy composition and Si-doping on vacancy defect formation in (In _x Ga _{1-x}) ₂ O ₃ thin films. <i>Journal of Applied Physics</i> , 2018 , 123, 125705	2.5	6
45	Wavelength-selective ultraviolet (Mg,Zn)O photodiodes: Tuning of parallel composition gradients with oxygen pressure. <i>Applied Physics Letters</i> , 2016 , 108, 243503	3.4	6
44	Microscopic Identification of Hot Spots in Multibarrier Schottky Contacts on Pulsed Laser Deposition Grown Zinc Oxide Thin Films. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 536-541	2.9	6
43	Electronic defects in In ₂ O ₃ and In ₂ O ₃ :Mg thin films on r-plane sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 2304-2308	1.3	6
42	Modal gain and its diameter dependence in single-ZnO micro- and nanowires. <i>Semiconductor Science and Technology</i> , 2012 , 27, 015005	1.8	6
41	The E3 Defect in Mg _x Zn _{1-x} O. <i>Journal of Electronic Materials</i> , 2010 , 39, 584-588	1.9	6
40	Electrical and optical spectroscopy on ZnO:Co thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 157-160	2.6	6
39	All-Oxide Transparent Thin-Film Transistors Based on Amorphous Zinc Tin Oxide Fabricated at Room Temperature: Approaching the Thermodynamic Limit of the Subthreshold Swing. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000423	6.4	6
38	Controlled formation of Schottky diodes on n-doped ZnO layers by deposition of p-conductive polymer layers with oxidative chemical vapor deposition. <i>Nano Express</i> , 2020 , 1, 010013	2	5
37	Transparent Conductive Oxides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1408-1408	1.6	5
36	Nickel-related defects in ZnO [A deep-level transient spectroscopy and photo-capacitance study. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 1949-1955	1.3	5
35	Shallow Donors and Compensation in Homoepitaxial ZnO Thin Films. <i>Journal of Electronic Materials</i> , 2010 , 39, 595-600	1.9	5

34	Synthesis and physical properties of cylindrite micro tubes and lamellae. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1335-1350	1.3	5
33	Cathodoluminescence of large-area PLD grown ZnO thin films measured in transmission and reflection. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 89-93	2.6	5
32	High-Quality Schottky Barrier Diodes on Γ Gallium Oxide Thin Films on Glass Substrate. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3126-Q3132	2	4
31	Investigation of acceptor states in ZnO by junction DLTS. <i>Superlattices and Microstructures</i> , 2007 , 42, 14-20	2.8	4
30	Pulsed laser deposition of Fe- and Fe, Cu-doped ZnO thin films. <i>Annalen Der Physik</i> , 2004 , 13, 57-58	2.6	4
29	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. <i>Journal of Physics Condensed Matter</i> , 2020 ,	1.8	4
28	Ring Oscillators Based on ZnO Channel JFETs and MESFETs. <i>Advanced Electronic Materials</i> , 2016 , 2, 1500631	4.1	4
27	Effect of Annealing on the Band Alignment of ALD SiO ₂ on (Al _x Ga _{1-x}) ₂ O ₃ for x = 0.2 - 0.65. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P751-P756	2	4
26	Realization of highly rectifying Schottky barrier diodes and pn heterojunctions on Γ Ga ₂ O ₃ by overcoming the conductivity anisotropy. <i>Journal of Applied Physics</i> , 2021 , 130, 084502	2.5	4
25	Aluminium- and gallium-doped homoepitaxial ZnO thin films: Strain-engineering and electrical performance. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1440-1447	1.6	3
24	Changes in band alignment during annealing at 600 °C of ALD Al ₂ O ₃ on (In _x Ga _{1-x}) ₂ O ₃ for x = 0.25-0.74. <i>Journal of Applied Physics</i> , 2020 , 127, 105701	2.5	3
23	Negative-U Properties of the Deep Level E ₃ in ZnO. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700670	1.3	3
22	Gate- and drain-lag effects in (Mg,Zn)O-based metal-semiconductor field-effect transistors. <i>Journal of Applied Physics</i> , 2011 , 109, 074515	2.5	3
21	. <i>IEEE Electron Device Letters</i> , 2011 , 32, 515-517	4.4	3
20	Donor-Acceptor pair recombination in non-stoichiometric ZnO thin films. <i>Solid State Communications</i> , 2010 , 150, 379-382	1.6	3
19	Ultrahigh-performance integrated inverters based on amorphous zinc tin oxide deposited at room temperature. <i>APL Materials</i> , 2020 , 8, 091111	5.7	3
18	Evidence for oxygen being a dominant shallow acceptor in p-type CuI. <i>APL Materials</i> , 2021 , 9, 051101	5.7	3
17	Temperature dependent self-compensation in Al- and Ga-doped Mg _{0.05} Zn _{0.95} O thin films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2016 , 120, 205703	2.5	3

16	Properties of In ₂ S ₃ -Based pin-Heterojunctions. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700827	1.6	2
15	Impact of strain on electronic defects in (Mg,Zn)O thin films. <i>Journal of Applied Physics</i> , 2014 , 116, 103703	3.5	2
14	Gas phase synthesis of ionic solid solutions-crystalline bulk materials and thin films. <i>Progress in Solid State Chemistry</i> , 2009 , 37, 57-69	8	2
13	Structural characterization of H plasma-doped ZnO single crystals by Hall measurements and photoluminescence studies. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 2426-2431	1.6	2
12	Identification of LiNi and VNi acceptor levels in doped nickel oxide. <i>APL Materials</i> , 2020 , 8, 121106	5.7	2
11	p-Type Doping and Alloying of CuI Thin Films with Selenium. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021 , 15, 2100214	2.5	2
10	Electron transport mechanism in rf-sputtered amorphous zinc oxynitride thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1767-1773	1.6	2
9	Fermi level controlled point defect balance in ion irradiated indium oxide. <i>Journal of Applied Physics</i> , 2021 , 130, 085703	2.5	2
8	Dynamics of exciton-polariton emission in CuI. <i>APL Materials</i> , 2021 , 9, 121102	5.7	2
7	Defect studies on Ar-implanted ZnO thin films. <i>Physica Status Solidi (B): Basic Research</i> , 2014 , 251, 937-941	3	1
6	Epitaxial Growth of (Al _x Ga _{1-x}) ₂ O ₃ Layers and Superlattice Heterostructures up to x = 0.48 on Highly Conductive Al-Doped ZnO Thin-Film Templates by Pulsed Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000359	1.3	1
5	Strain states and relaxation for (α)-(Al _x Ga _{1-x}) ₂ O ₃ thin films on prismatic planes of (α)-Al ₂ O ₃ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt. <i>Journal of Materials Research</i> , 1	2.5	1
4	Tuning material properties of amorphous zinc oxynitride thin films by magnesium addition. <i>APL Materials</i> , 2021 , 9, 021120	5.7	0
3	Quantum Confined Stark Effect of Excitons Localized at Very Thin InAs Layers Embedded in GaAs. <i>Physica Status Solidi A</i> , 2002 , 190, 709-713		
2	Numerical Modeling of Schottky Barrier Diode Characteristics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2100121	1.6	
1	Epitaxial lift-off of single crystalline CuI thin films. <i>Journal of Materials Chemistry C</i> , 2022 , 10, 4124-4127	7.1	